

**描述 / Descriptions**

DFN 3\*3A-8L 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a DFN 3\*3A-8L Plastic Package.

**特征 / Features**

$V_{DS} (V) = -30V$

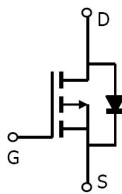
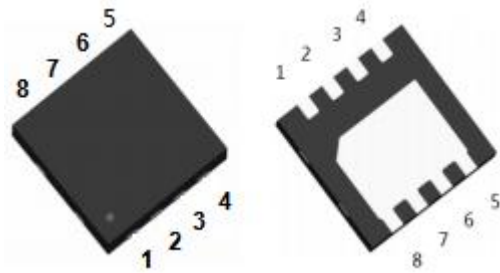
$I_D = -19 A (V_{GS} = -20V)$

无卤产品。HF Product.

**用途 / Applications**

用于电源管理，便携式设备和电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

**内部等效电路 / Equivalent Circuit****引脚排列 / Pinning**

| 出脚   | 定义 |
|------|----|
| Pin1 | S  |
| Pin2 | S  |
| Pin3 | S  |
| Pin4 | G  |
| Pin5 | D  |
| Pin6 | D  |
| Pin7 | D  |
| Pin8 | D  |

**印章代码 / Marking**

见印章说明 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

| 参数<br>Parameter                        | 符号<br>Symbol                  | 数值<br>Rating | 单位<br>Unit         |
|----------------------------------------|-------------------------------|--------------|--------------------|
| Drain-Source Voltage                   | $V_{DSS}$                     | -30          | V                  |
| Gate-Source Voltage                    | $V_{GSS}$                     | $\pm 20$     | V                  |
| Continuous Drain Current               | $I_D (T_a=25^\circ\text{C})$  | -19          | A                  |
| Continuous Drain Current               | $I_D (T_a=70^\circ\text{C})$  | -14          | A                  |
| Pulsed Drain Current                   | $I_{DM}$                      | -56          | A                  |
| Avalanche energy L=0.5mH               | $E_{AS}$                      | 170          | mJ                 |
| Power Dissipation for Single Operation | $P_D (T_a=25^\circ\text{C})$  | 13           | W                  |
| Power Dissipation for Single Operation | $P_D (T_a=100^\circ\text{C})$ | 5.2          | W                  |
| Maximum Junction Temperature           | $T_j$                         | 150          | $^\circ\text{C}$   |
| Storage Temperature Range              | $T_{stg}$                     | -55 ~ 150    | $^\circ\text{C}$   |
| Thermal Resistance-Junction to Ambient | $R_{\theta JA} (t \leq 10s)$  | 35           | $^\circ\text{C/W}$ |
| Thermal Resistance-Junction to Ambient | $R_{\theta JA}$               | 67           | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case               | $R_{\theta JC}$               | 9.6          | $^\circ\text{C/W}$ |

## 电性能参数 / Electrical Characteristics(Ta=25°C)

| 参数<br>Parameter                   | 符号<br>Symbol  | 测试条件<br>Test Conditions                                                  | 最小值<br>Min | 典型值<br>Typ | 最大值<br>Max | 单位<br>Unit |
|-----------------------------------|---------------|--------------------------------------------------------------------------|------------|------------|------------|------------|
| Drain-Source Breakdown Voltage    | $BV_{DSS}$    | $I_D = -250\mu A$ $V_{GS} = 0V$                                          | -30        |            |            | V          |
| Zero Gate Voltage Drain Current   | $I_{DSS}$     | $V_{DS} = -30V$ $V_{GS} = 0V$                                            |            |            | -1.0       | $\mu A$    |
|                                   |               | $V_{DS} = -30V$ $V_{GS} = 0V$<br>$T_J = 55^\circ C$                      |            |            | -5.0       |            |
| Gate-Body leakage current         | $I_{GSS}$     | $V_{DS} = 0V$ $V_{GS} = \pm 20V$                                         |            |            | $\pm 100$  | nA         |
| Gate Threshold Voltage            | $V_{GS(th)}$  | $V_{DS} = V_{GS}$ $I_D = -250\mu A$                                      | -1.0       | -1.7       | -3.0       | V          |
| Static Drain-Source On-Resistance | $R_{DS(on)}$  | $V_{GS} = -10V$ $I_D = -10A$                                             |            | 17.8       | 20         | m $\Omega$ |
|                                   |               | $V_{GS} = -4.5V$ $I_D = -10A$                                            |            | 28.5       | 30         |            |
| Forward Transconductance          | $g_{FS}$      | $V_{DS} = -5V$ $I_D = -8.8A$                                             |            | 11         |            | S          |
| Diode Forward Voltage             | $V_{SD}$      | $I_S = -1A$ $V_{GS} = 0V$                                                |            | -0.72      | -1.0       | V          |
| Total Gate Charge                 | $Q_{g(10V)}$  | $V_{GS} = -10V$ $V_{DS} = -15V$<br>$I_D = -10A$                          |            | 19         | 30         | nC         |
| Total Gate Charge                 | $Q_{g(4.5V)}$ |                                                                          |            | 9.6        | 20         |            |
| Gate-Source Charge                | $Q_{gs}$      |                                                                          |            | 3.5        |            |            |
| Gate-Drain Charge                 | $Q_{gd}$      |                                                                          |            | 4.5        |            |            |
| Gate Resistance                   | $R_g$         | $V_{GS} = 0V$ $f = 1MHz$ $V_{DS} = 0V$                                   |            | 8.8        |            | $\Omega$   |
| Input Capacitance                 | $C_{iss}$     | $V_{GS} = 0V$ $f = 1MHz$ $V_{DS} = -25V$                                 |            | 1770       |            | pF         |
| Output Capacitance                | $C_{oss}$     |                                                                          |            | 550        |            |            |
| Reverse Transfer Capacitance      | $C_{rss}$     |                                                                          |            | 290        |            |            |
| Turn-on Delay Time                | $t_{d(ON)}$   | $V_{GS} = -10V$ $V_{DS} = -15V$<br>$R_L = 1.5\Omega$ $R_{GEN} = 3\Omega$ |            | 10         |            | ns         |
| Turn-on Rise Time                 | $t_r$         |                                                                          |            | 5.5        |            |            |
| Turn-off Delay Time               | $t_{d(OFF)}$  |                                                                          |            | 26         |            |            |
| Turn-off Fall Time                | $t_f$         |                                                                          |            | 9          |            |            |

## 电参数曲线图 / Electrical Characteristic Curve

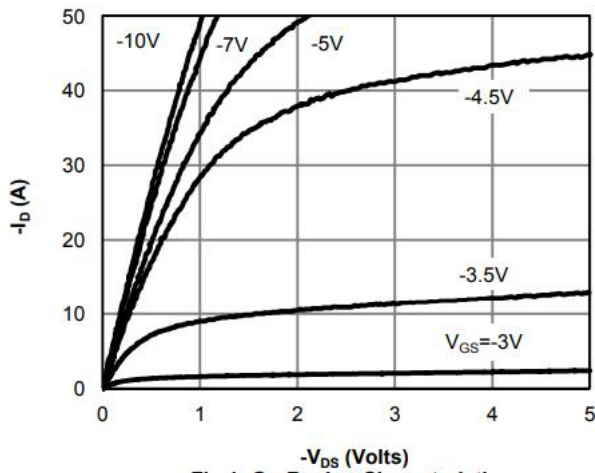


Fig 1: On-Region Characteristics

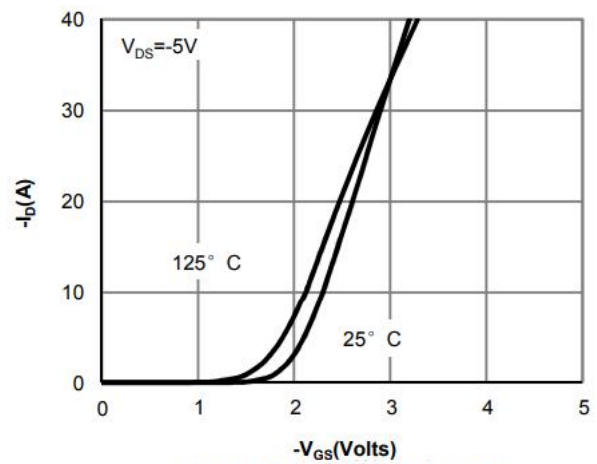


Figure 2: Transfer Characteristics

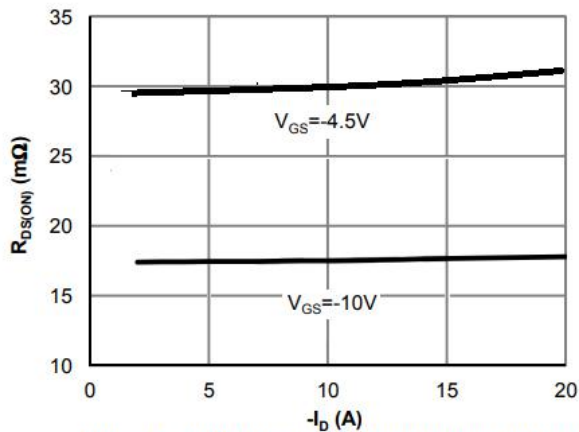


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

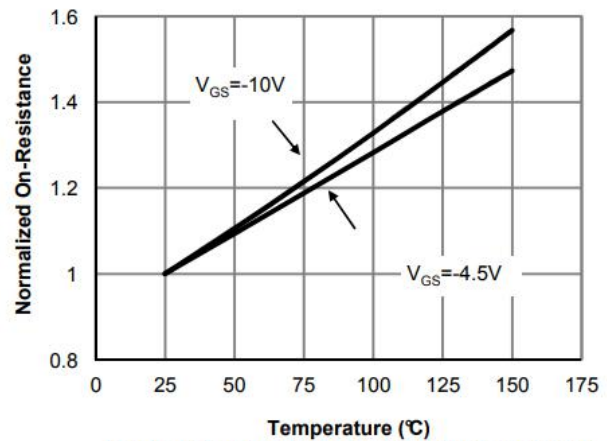


Figure 4: On-Resistance vs. Junction Temperature

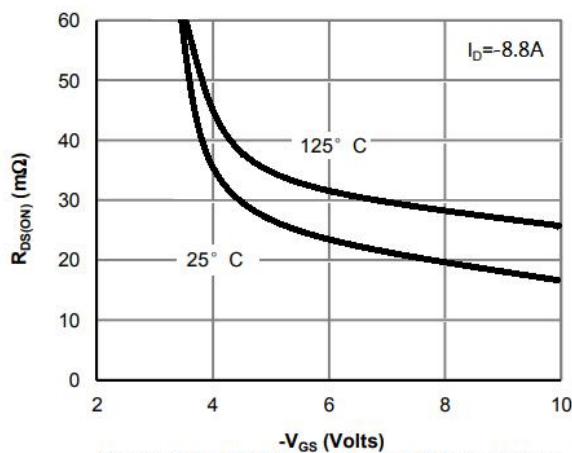


Figure 5: On-Resistance vs. Gate-Source Voltage

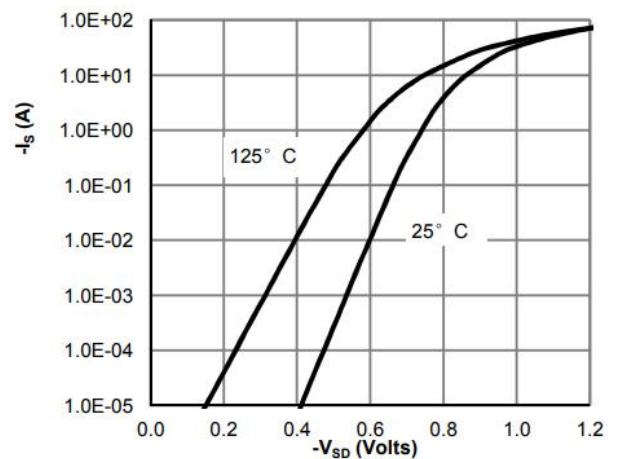
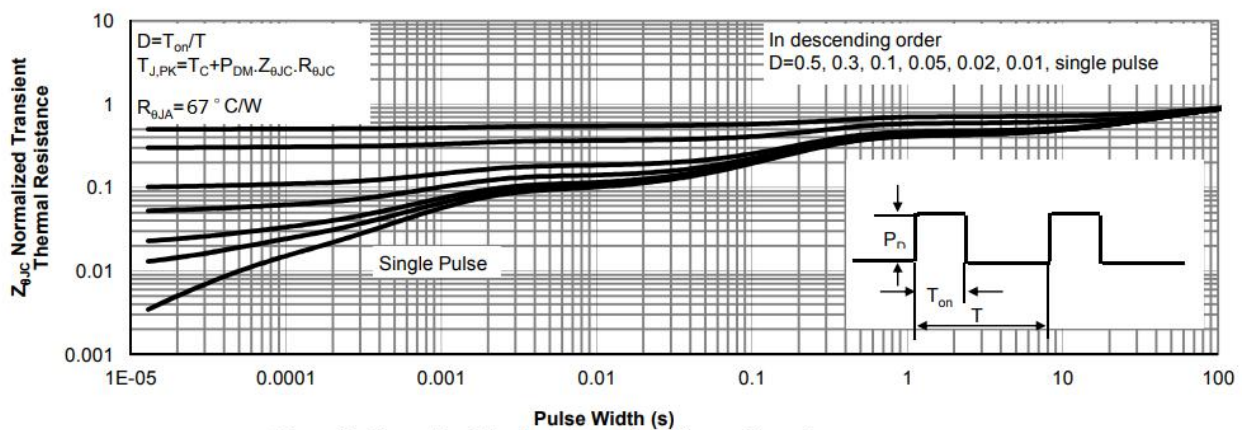
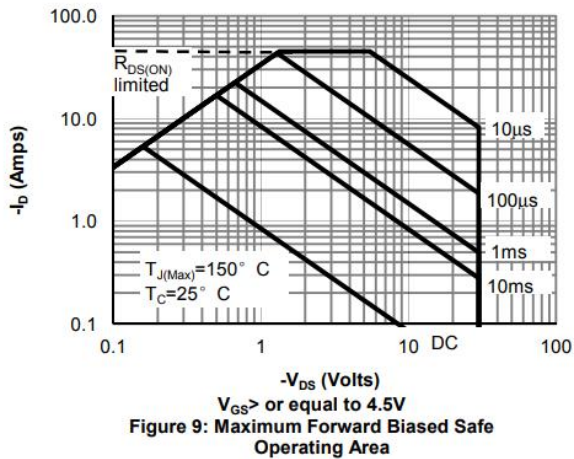
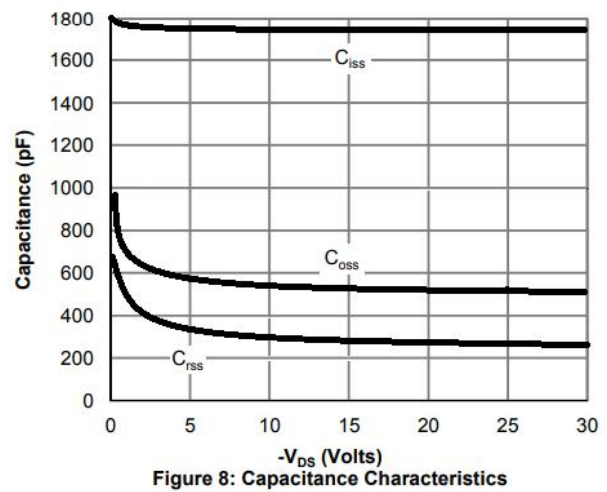
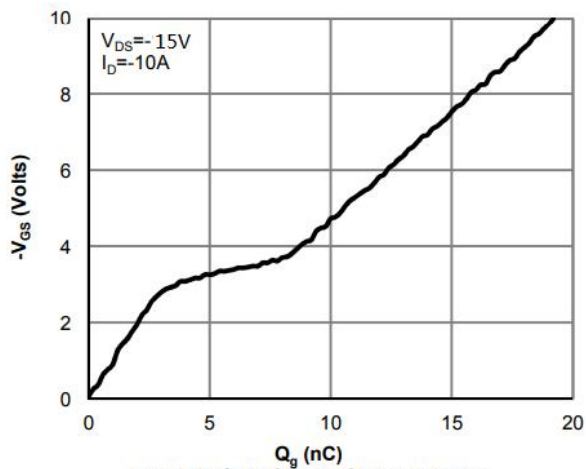


Figure 6: Body-Diode Characteristics

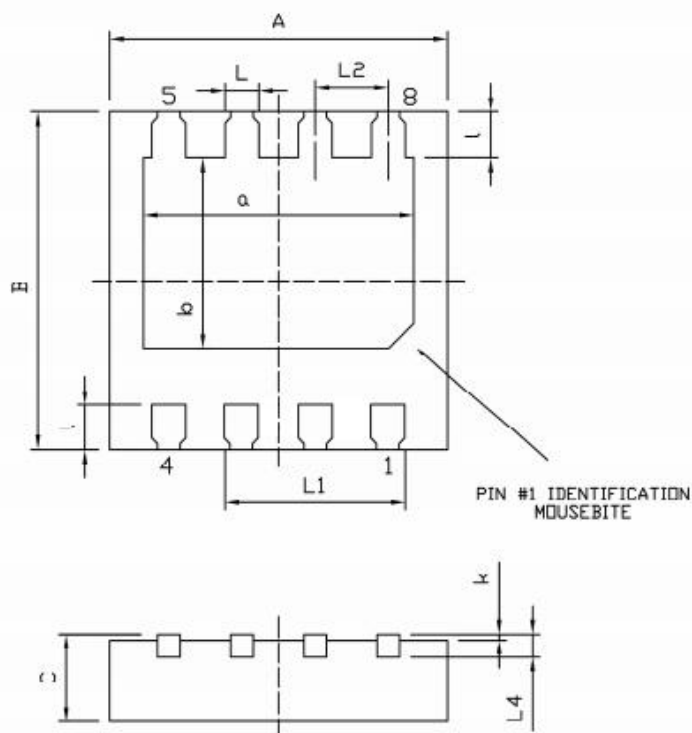
## 电参数曲线图 / Electrical Characteristic Curve



## 外形尺寸图 / Package Dimensions

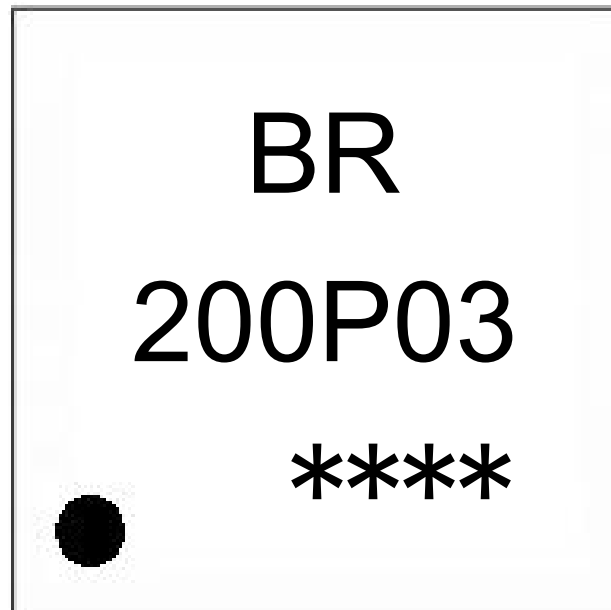
DFN3X3A-8L

Unit:mm



| Dimensions In<br>Millimeterer |      |      |      |
|-------------------------------|------|------|------|
| Symbol                        | MIN  | TYP  | MAX  |
| A                             | 2.90 | 3.00 | 3.10 |
| B                             | 2.90 | 3.00 | 3.10 |
| C                             | 0.70 | 0.75 | 0.80 |
| L                             | 0.25 | 0.30 | 0.35 |
| L1                            | 1.55 | 1.60 | 1.65 |
| L2                            | -    | 0.65 | -    |
| L4                            | 0.19 | 0.20 | 0.21 |
| a                             | 2.30 | 2.40 | 2.50 |
| b                             | 1.60 | 1.70 | 1.80 |
| k                             | 0.00 | -    | 0.05 |
| l                             | 0.35 | 0.40 | 0.45 |

印章说明 / Marking Instructions



说明：

BR： 为公司代码

200P03： 为型号代码

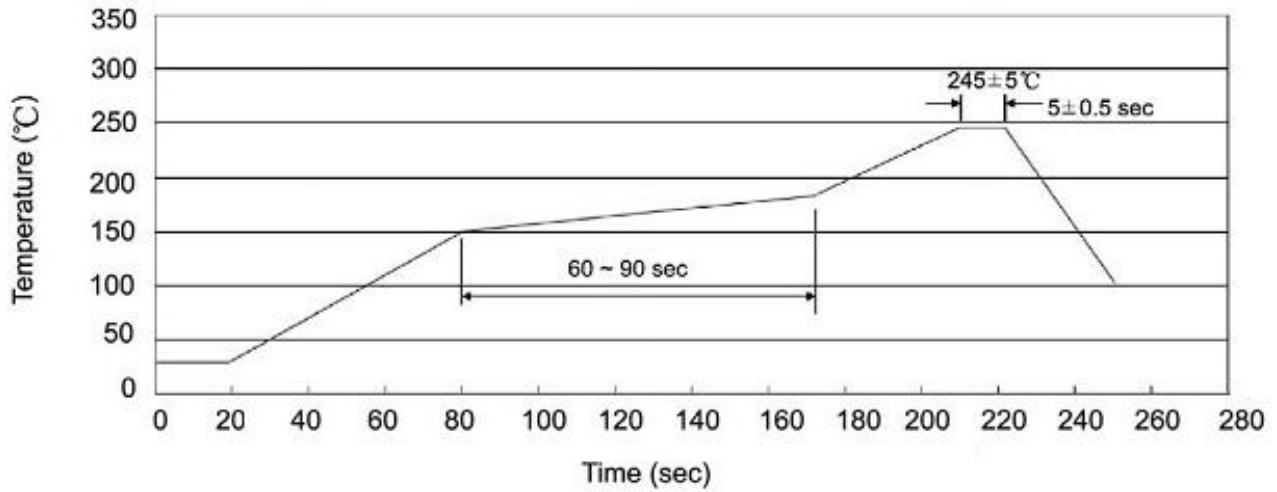
\*\*\*\*\*： 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.

200P03: Product Type

\*\*\*\*\*: Lot No. Code, code change with Lot No.

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec；
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

| Package Type<br>封装形式 | Units 包装数量         |                         |                        |                              |                        | Dimension 包装尺寸 (unit: mm <sup>3</sup> ) |             |             |
|----------------------|--------------------|-------------------------|------------------------|------------------------------|------------------------|-----------------------------------------|-------------|-------------|
|                      | Units/Reel<br>只/卷盘 | Reels/Inner Box<br>卷盘/盒 | Units/Inner Box<br>只/盒 | Inner Boxes/Outer Box<br>盒/箱 | Units/Outer Box<br>只/箱 | Reel                                    | Inner Box 盒 | Outer Box 箱 |
| DFN 3*3-8L           | 5,000              | 2                       | 10,000                 | 6                            | 60,000                 | 13" ×12                                 | 360×360×50  | 380×335×366 |

**使用说明 / Notices**